

FOR PTO-1449 (Modified)

**LIST OF PATENTS AND PUBLICATIONS FOR
APPLICANTS INFORMATION DISCLOSURE
STATEMENT**

(Use several sheets if necessary)

ATTY. DOCKET NO.

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09/941,817

APPLICANT

APPLICANT **COPY OF PAPERS**
~~SOMIT TALWAR, et al.~~ **ORIGINALLY FILED**

FILING DATE

August 29, 2001

GROUP

2812

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

8 TEACHERS

FOREIGN PATENT DOCUMENTS

OTHER

ART (Including Author, Title, Date, Pertinent Pages, Etc.)

<i>D</i>	B	Somit Talwar, Gaurav Verma, Kurt Weiner, <i>Ultra-Shallow, Abrupt, and Highly-Activated Junctions by Low-Energy Ion Implantation and Laser Annealing</i> , IEEE, 1999, pp. 1171-1174
<i>D</i>	C	P.S. Peercy, J. Y. Tsao, S. R. Stiffler and Michael O. Thompson, <i>Explosive Crystallization in Amorphous Si Initiated by Long Pulse Width Laser Irradiation</i> , Appl. Phys. Lett. 52 (3), January 18, 1988, pp 203-205

EXAMINER

DATE CONSIDERED

12-08-02

EXAMINER:

Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.